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FIG. 31

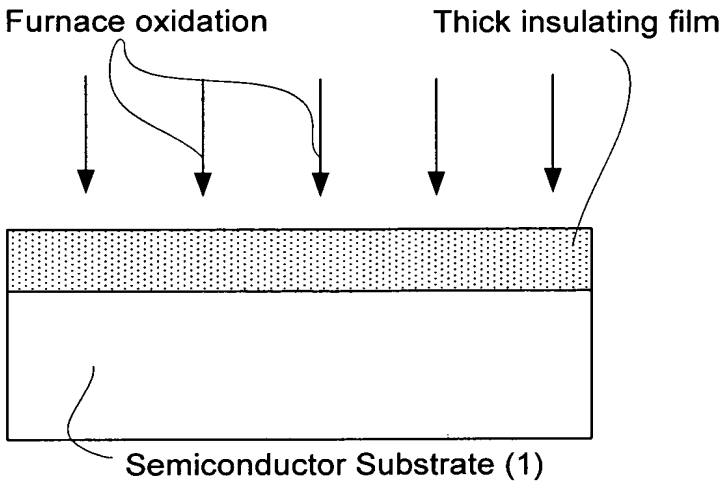



FIG. 32

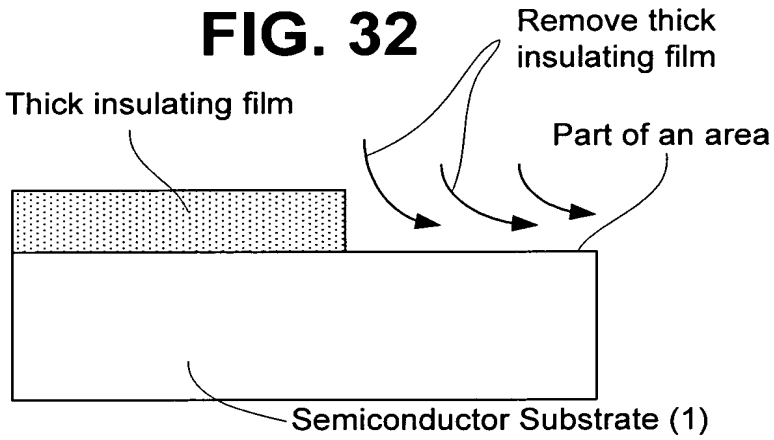
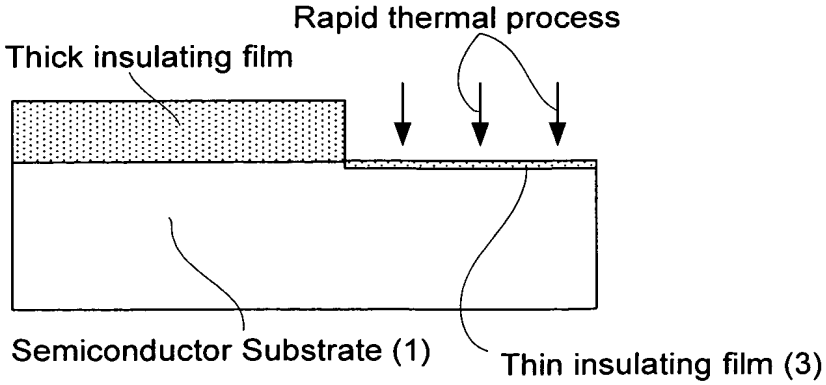



FIG. 33



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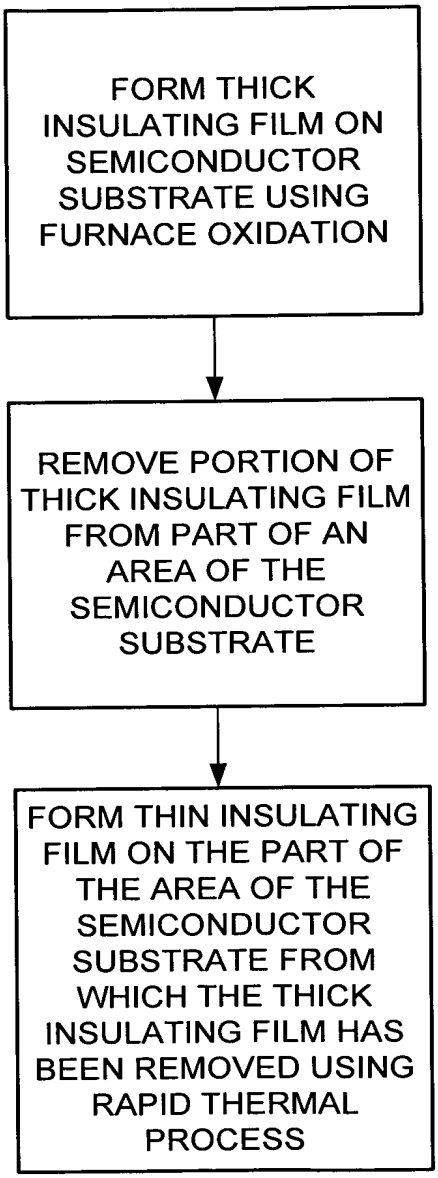
# FIG. 34


FORM THICK INSULATING FILM ON SEMICONDUCTOR SUBSTRATE USING FURNACE OXIDATION
REMOVE PORTION OF THICK INSULATING FILM FROM PART OF AN AREA OF THE SEMICONDUCTOR SUBSTRATE
FORM THIN INSULATING FILM ON THE PART OF THE AREA OF THE SEMICONDUCTOR SUBSTRATE FROM WHICH THE THICK INSULATING FILM HAS BEEN REMOVED USING RAPID THERMAL PROCESS